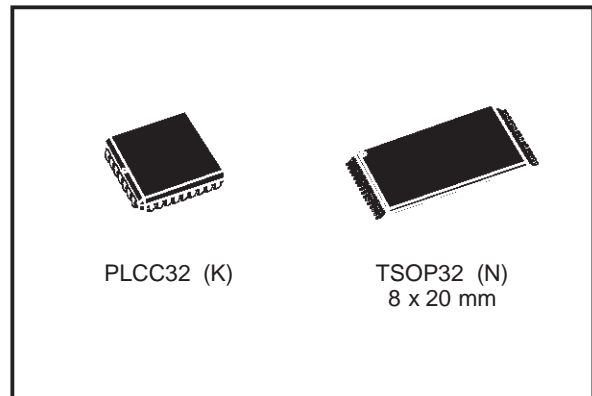




2 Mbit (256Kb x8, Bulk) Low Voltage Flash memory

DATA BRIEFING

- 2.7V to 3.6V SUPPLY VOLTAGE
- 12V PROGRAMMING VOLTAGE
- FAST ACCESS TIME: 100ns
- BYTE PROGRAMMING TIME: 10 μ s typical (PRESTO F Algorithm)
- ELECTRICAL CHIP ERASE in 1s RANGE
- LOW POWER CONSUMPTION
 - Active Current: 15mA max.
 - Stand-by Current: 7 μ A typ.
- 10,000 PROGRAM/ERASE CYCLES
- INTEGRATED ERASE/PROGRAM-STOP TIMER
- OTP COMPATIBLE PACKAGES and PINOUTS
- 20 YEARS DATA RETENTION
 - Defectivity below 1ppm/year
- ELECTRONIC SIGNATURE
 - Manufacturer Code: 20h
 - Device Code: F5h



DESCRIPTION

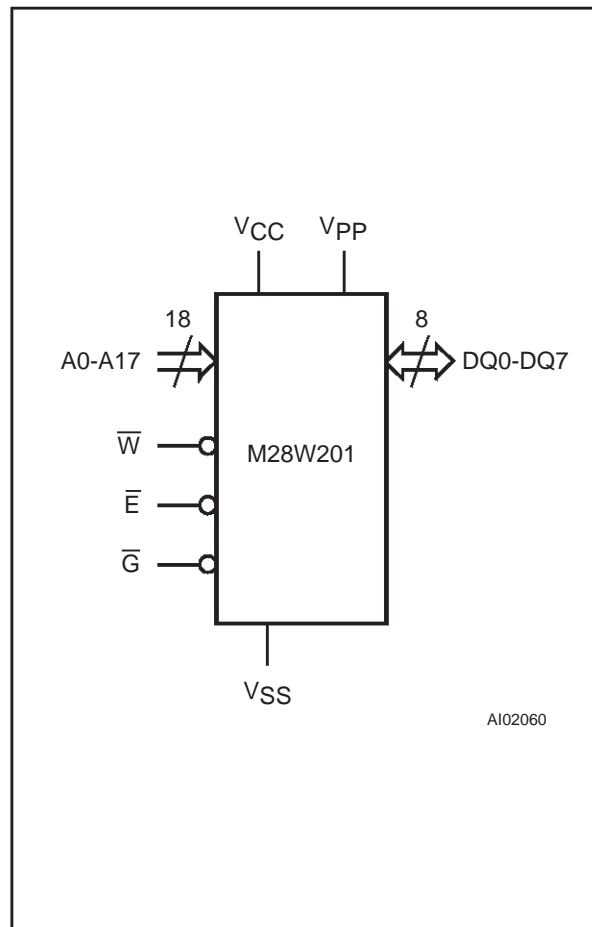
The M28W201 Flash memory product is a non-volatile memories which may be erased electrically at the chip level and programmed byte-by-byte. It is organised as 256 Kbytes. It uses a command register architecture to select the operating modes and thus provide a simple microprocessor interface.

The device is offered in PLCC32 and TSOP32 (8 x 20mm) package.

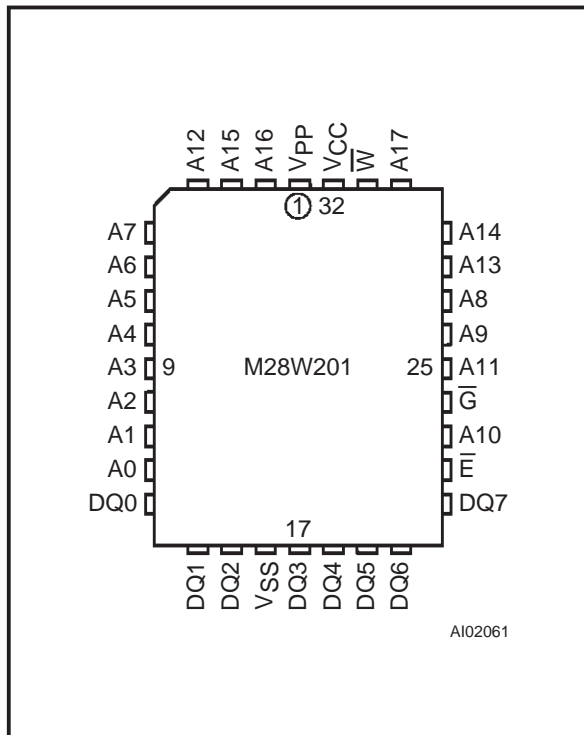
Signal Names

A0 - A17	Address Inputs
DQ0 - DQ7	Data Inputs / Outputs
\bar{E}	Chip Enable
\bar{G}	Output Enable
\bar{W}	Write Enable
V _{PP}	Program Supply
V _{CC}	Supply Voltage
V _{SS}	Ground

Logic Diagram



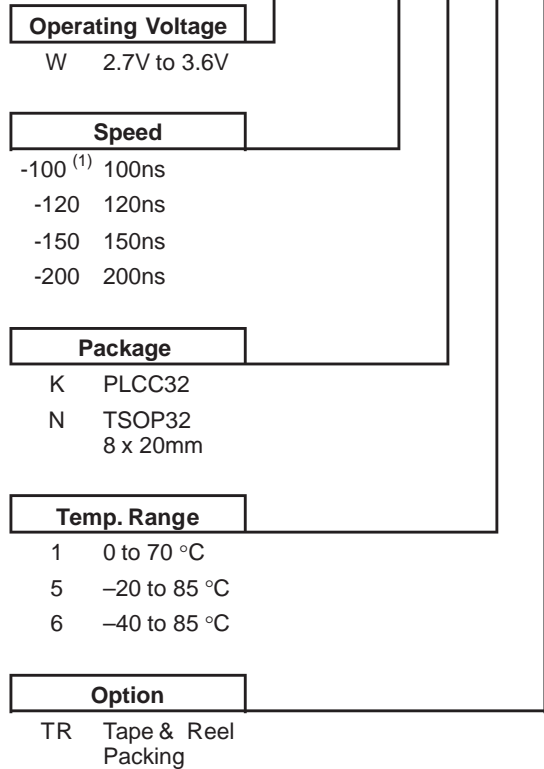
LCC Pin Connections



Ordering Information Scheme

For a list of available options or for further information on any aspect of this device, please contact the STMicroelectronics Sales Office nearest to you.

Example: M28W201 -150 N 1 TR



Notes: 1. This speed is obtained with a supply voltage range of $V_{CC} = 3.3V \pm 0.3V$ and a load capacitance at 30pF.

Devices are shipped from the factory with the memory content erased (to FFh).

TSOP Pin Connections

